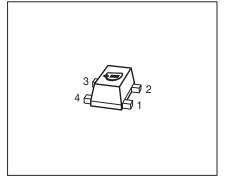


Low Noise Silicon Bipolar RF Transistor

- For low current applications
- Minimum noise figure NF_{\min} = 1.25 dB at 1.8 GHz Outstanding G_{\max} = 22.5 dB at 1.8 GHz
- Transition frequency f_T = 25 GHz
- Pb-free (RoHS compliant) and halogen-free thin small flat package (1.4 x 0.8 x 0.59 mm) with visible leads
- Qualification report according to AEC-Q101 available







ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Туре	Marking	Pin Configuration				Package		
BFP405F	ALs	1=B	2=E	3=C	4=E	-	-	TSFP-4

Maximum Ratings at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}		V
<i>T</i> _A = 25 °C		4.5	
<i>T</i> _A = -55 °C		4.1	
Collector-emitter voltage	V _{CES}	15	
Collector-base voltage	V_{CBO}	15	
Emitter-base voltage	V _{EBO}	1.5	
Collector current	I _C	25	mA
Base current	l _B	3	
Total power dissipation ¹⁾	P _{tot}	75	mW
<i>T</i> _S ≤ 112 °C			
Junction temperature	T_{J}	150	°C
Storage temperature	T _{Stg}	-55 150	

 $^{^{\}rm 1}T_{\rm S}$ is measured on the emitter lead at the soldering point to the pcb

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R _{thJS}	500	K/W



Electrical Characteristics at $T_{\rm A}$ = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit	
		min.	typ.	max.		
DC Characteristics						
Collector-emitter breakdown voltage	V _{(BR)CEO}	4	5	-	V	
$I_{\rm C}$ = 1 mA, $I_{\rm B}$ = 0						
Collector-emitter cutoff current	I _{CES}	-	-	10	μA	
$V_{CE} = 15 \text{ V}, V_{BE} = 0$						
Collector-base cutoff current	I _{CBO}	-	-	100	nA	
$V_{CB} = 5 \text{ V}, I_{E} = 0$						
Emitter-base cutoff current	I _{EBO}	-	-	1	μA	
$V_{\rm EB}$ = 0.5 V, $I_{\rm C}$ = 0						
DC current gain	h _{FE}	60	95	130	-	
$I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 4 V, pulse measured						

 $^{^{1}\}mathrm{For}$ the definition of R_{thJS} please refer to Application Note AN077 (Thermal Resistance Calculation)



Electrical Characteristics at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random samplin	g)				
Transition frequency	f_{T}	18	25	-	GHz
$I_{\rm C}$ = 10 mA, $V_{\rm CE}$ = 3 V, f = 2 GHz					
Collector-base capacitance	C_{cb}	-	0.05	0.1	pF
$V_{\text{CB}} = 2 \text{ V}, f = 1 \text{ MHz}, V_{\text{BE}} = 0$,					
emitter grounded					
Collector emitter capacitance	C _{ce}	-	0.2	-	
$V_{CE} = 2 \text{ V}, f = 1 \text{ MHz}, V_{BE} = 0$,					
base grounded					
Emitter-base capacitance	C _{eb}	-	0.25	-	
$V_{\text{EB}} = 0.5 \text{ V}, f = 1 \text{ MHz}, V_{\text{CB}} = 0$,					
collector grounded					
Minimum noise figure	NF _{min}	-	1.25	-	dB
I_{C} = 2 mA, V_{CE} = 2 V, f = 1.8 GHz, Z_{S} = Z_{Sopt}					
Power gain, maximum stable ¹⁾	G _{ms}	-	22.5	-	dB
$I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 2 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$,					
$Z_{L} = Z_{Lopt}$, $f = 1.8 \text{ GHz}$					
Insertion power gain	$ S_{21} ^2$	-	18	-	
$V_{CE} = 2 \text{ V}, I_{C} = 5 \text{ mA}, f = 1.8 \text{ GHz},$					
$Z_{\rm S} = Z_{\rm L} = 50 \ \Omega$					
Third order intercept point at output ²⁾	IP3	-	14	-	dBm
V_{CE} = 2 V, I_{C} = 5 mA, f = 1.8 GHz,					
$Z_{\rm S} = Z_{\rm L} = 50~\Omega$					
1dB compression point at output	P _{-1dB}	-	0	-	
$I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 2 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 Ω ,					
f = 1.8 GHz					
	•	•	•	•	•

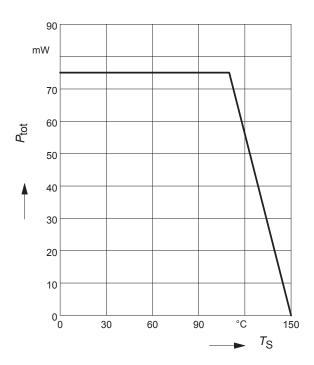
 $^{{}^{1}}G_{\rm ms} = |S_{21} / S_{12}|$

²IP3 value depends on termination of all intermodulation frequency components.

Termination used for this measurement is 50Ω from 0.1 MHz to 6 GHz



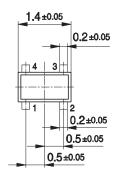
Total power dissipation $P_{tot} = f(T_S)$

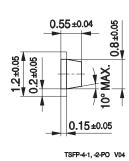




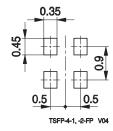
Package Outline



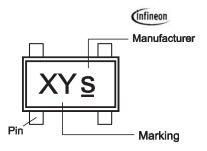




Foot Print

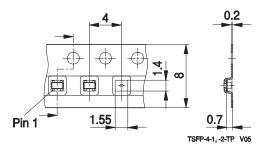


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel





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